

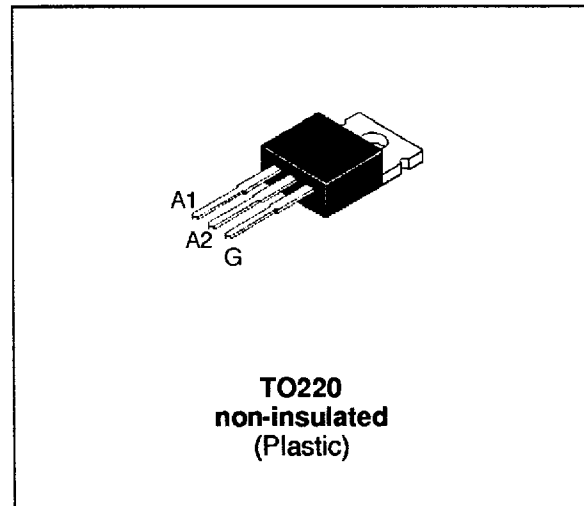
STANDARD TRIACS

FEATURES

- $I_{T(RMS)} = 25A$
- $V_{DRM} = 400V$ to $800V$
- High surge current capability

DESCRIPTION

The T25xxxH series of triacs uses a high performance MESA GLASS technology. These parts are intended for general purpose switching and phase control applications.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
$I_{T(RMS)}$	RMS on-state current (360° conduction angle)	$T_c = 80^\circ C$	25	A
I_{TSM}	Non repetitive surge peak on-state current (T_j initial = $25^\circ C$)	$t_p = 8.3$ ms	262	A
		$t_p = 10$ ms	250	
I^2t	I^2t Value for fusing	$t_p = 10$ ms	312	A^2s
di/dt	Critical rate of rise of on-state current $I_G = 500$ mA $di_G/dt = 1$ A/ μs .	Repetitive F = 50 Hz	10	A/ μs
		Non Repetitive	50	
T_{stg} T_j	Storage and operating junction temperature range		- 40, + 150 - 40, + 125	$^\circ C$
TI	Maximum lead temperature for soldering during 10s at 4.5mm from case		260	$^\circ C$

Symbol	Parameter	Voltage				Unit
		D	M	S	N	
V_{DRM} V_{RRM}	Repetitive peak off-state voltage $T_j = 125^\circ C$	400	600	700	800	V

Fig.1 : Maximum RMS power dissipation versus RMS on-state current.

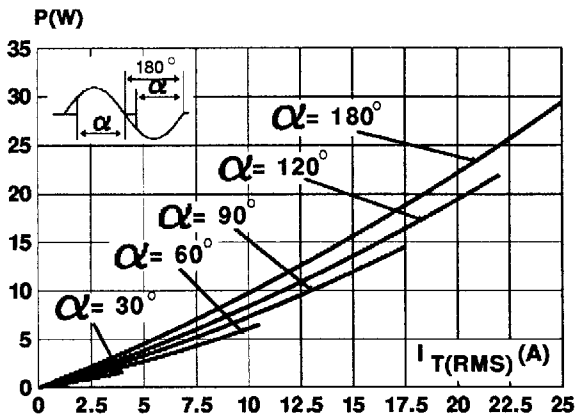


Fig.2 : Correlation between maximum RMS power dissipation and maximum allowable temperature (Tamb and Tcase) for different thermal resistances heatsink + contact.

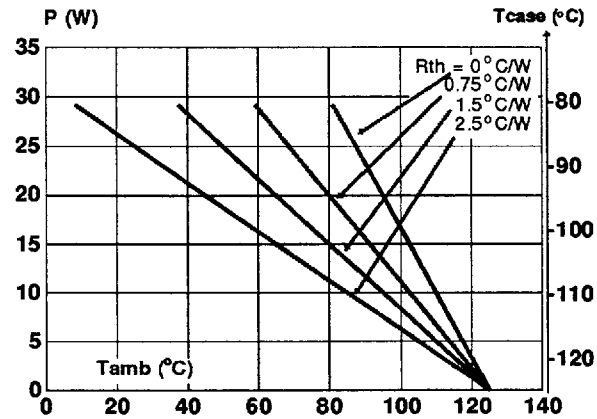


Fig.3 : RMS on-state current versus case temperature.

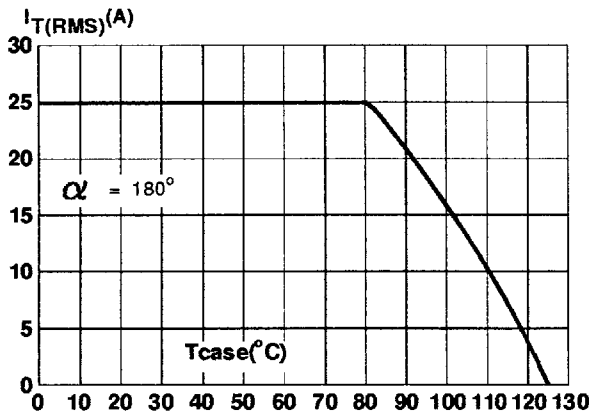


Fig.4 : Relative variation of thermal impedance versus pulse duration.

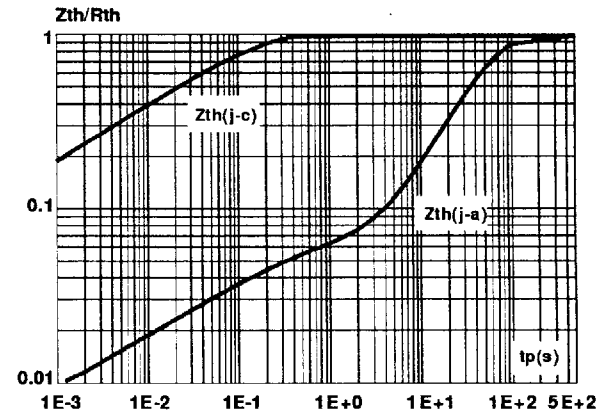


Fig.5 : Relative variation of gate trigger current and holding current versus junction temperature.

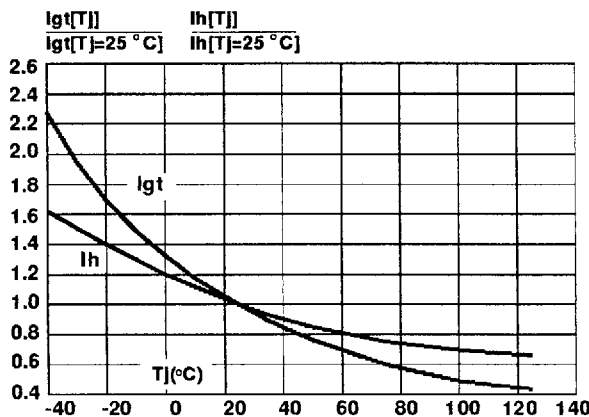


Fig.6 : Non repetitive surge peak on-state current versus number of cycles.

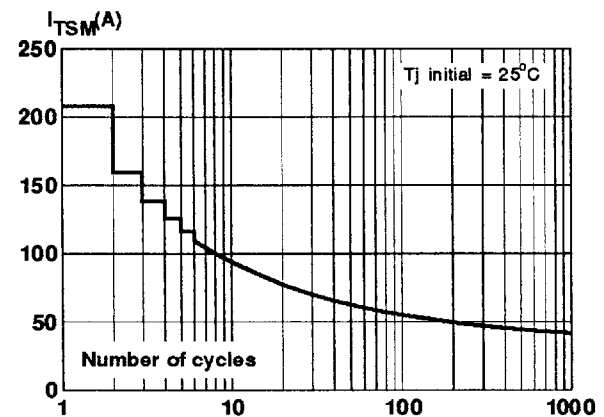


Fig.7 : Non repetitive surge peak on-state current for a sinusoidal pulse with width : $t \leq 10\text{ms}$, and corresponding value of I^2t .

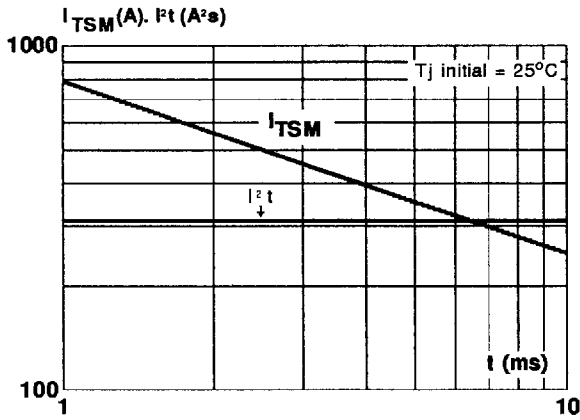
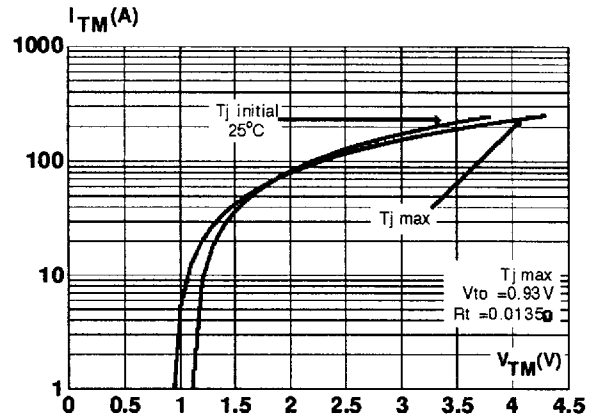
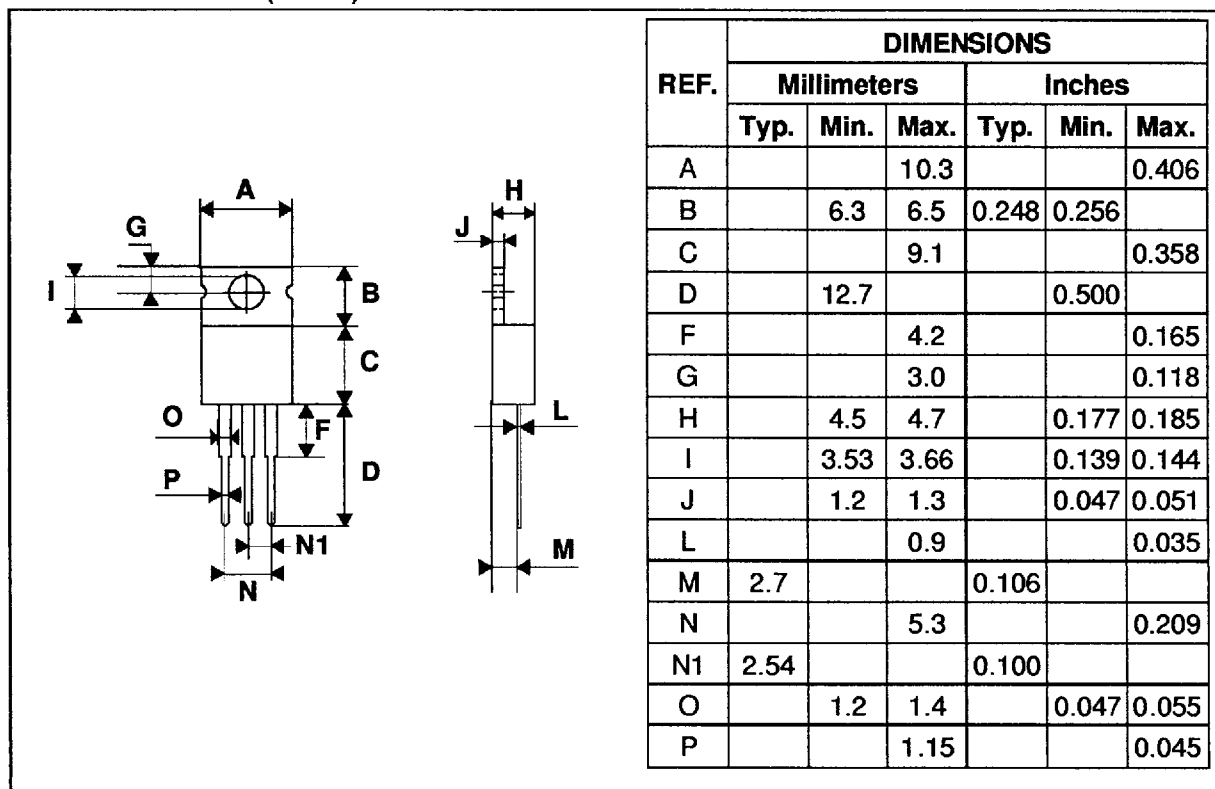


Fig.8 : On-state characteristics (maximum values).



PACKAGE MECHANICAL DATA
TO220 Non-insulated (Plastic)



Marking : type number
Weight : 1.8 g

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